NSN 5962-01-351-9525

Memory Microcircuit - Page 1 of 2

Between 0.220 inches and 0.310 inches

Overall Height: 0.400 inches Body Length: 1.060 inches Body Width:



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Between 0.130 inches and 0.185 inches Maximum Power Dissipation Rating: 2.0 watts Operating Tempurature Range: -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius End Application: Satellite communications terminal an/usc-3 (v) 1 Features Provided: Hermetically sealed and burn in and monolithic and programmed Inclosure Material: Ceramic Inclosure Configuration: Dual-in-line Output Logic Form: Transistor-transistor logic Input Circuit Pattern: 16 input Case Outline Source And Designator: D-8 mil-m-38510 Current Rating Per Characteristic: 185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal Test Data Document:	Body Height:
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Inclosure Material: Ceramic Inclosure Configuration: Dual-in-line Output Logic Form: Transistor-transistor logic Input Circuit Pattern: 16 input Case Outline Source And Designator: D-8 mil-m-38510 Current Rating Per Characteristic: 185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Features Provided:
Ceramic Inclosure Configuration: Dual-in-line Output Logic Form: Transistor-transistor logic Input Circuit Pattern: 16 input Case Outline Source And Designator: D-8 mil-m-38510 Current Rating Per Characteristic: 185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Hermetically sealed and burn in and monolithic and programmed
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Dual-in-line Output Logic Form: Transistor-transistor logic Input Circuit Pattern: 16 input Case Outline Source And Designator: D-8 mil-m-38510 Current Rating Per Characteristic: 185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Ceramic
Output Logic Form: Transistor-transistor logic Input Circuit Pattern: 16 input Case Outline Source And Designator: D-8 mil-m-38510 Current Rating Per Characteristic: 185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Inclosure Configuration:
Transistor-transistor logic Input Circuit Pattern: 16 input Case Outline Source And Designator: D-8 mil-m-38510 Current Rating Per Characteristic: 185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Dual-in-line
Input Circuit Pattern: 16 input Case Outline Source And Designator: D-8 mil-m-38510 Current Rating Per Characteristic: 185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Output Logic Form:
Case Outline Source And Designator: D-8 mil-m-38510 Current Rating Per Characteristic: 185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Transistor-transistor logic
Case Outline Source And Designator: D-8 mil-m-38510 Current Rating Per Characteristic: 185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Input Circuit Pattern:
D-8 mil-m-38510 Current Rating Per Characteristic: 185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	16 input
Current Rating Per Characteristic: 185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Case Outline Source And Designator:
185.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	D-8 mil-m-38510
Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Current Rating Per Characteristic:
Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	185.00 milliamperes reverse current, dc absolute
Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Terminal Surface Treatment:
And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Solder
Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Product Name:
-0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	And-or invert gate array
Time Rating Per Chacteristic: 45.00 nanoseconds delay Memory Device Type: Pal	Voltage Rating And Type Per Characteristic:
45.00 nanoseconds delay Memory Device Type: Pal	-0.5 volts power source and 7.0 volts power source
Memory Device Type: Pal	Time Rating Per Chacteristic:
Pal	45.00 nanoseconds delay
	Memory Device Type:
Test Data Document:	Pal
	Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.)	96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Terminal Type A	and Quantity	/ :
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20 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0